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# N-Channel 100 V (D-S) MOSFET

	PRODUCT	SUMMARY	
Ī	V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)
Ī	100	0.145 at V <sub>GS</sub> = 10 V	10

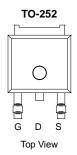
### **FEATURES**

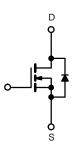
- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



### **APPLICATIONS**

· Primary Side Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)								
Parameter	Symbol	Limit	Unit					
Drain-Source Voltage	V <sub>DS</sub>	100	V					
Gate-Source Voltage	$V_{GS}$	± 20						
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	L	10					
	T <sub>C</sub> = 125 °C	· I <sub>D</sub>	5.7					
Pulsed Drain Current	I <sub>DM</sub>	30	Α					
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	10						
Avalanche Current	,				10			
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	12	mJ				
Maximum Dawar Dissination	T <sub>C</sub> = 25 °C	P <sub>D</sub>	55 <sup>b</sup>	10/				
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	' <sup>D</sup>	2.1 <sup>a</sup>	W				
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C				

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	D	16	20	°C/W	
Junction-to-Ambient*	Steady State	$R_{thJA}$	45	55		
Junction-to-Case		R <sub>thJC</sub>	2	2.4		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static					<u> </u>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	10			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.145	0.170	_	
5 1 2 2 2 2 1 5 1 1 h	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C			0.210		
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}, T_J = 175 \text{ °C}$		0.280	Ω		
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		25		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			1206		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		215			
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Total Gate Charge <sup>c</sup>	$Q_g$			19	24		
Gate-Source Charge <sup>c</sup>				5.1		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			7			
Gate Resistance	R <sub>g</sub>		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 80 \text{ V}, R_L = 5 \Omega$		35	55	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10A, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	25		
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				10	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, dI/dt = 100 A/μs		55	85	ns	

### Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

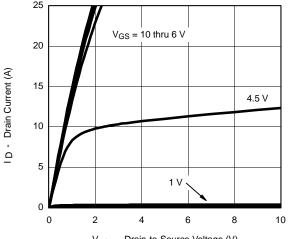
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





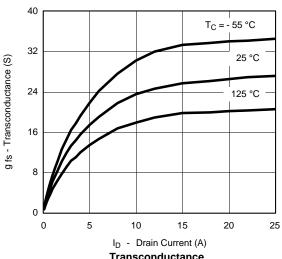
# TYPICAL CHARACTERISTICS (25 °C unless noted)



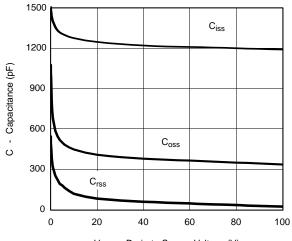


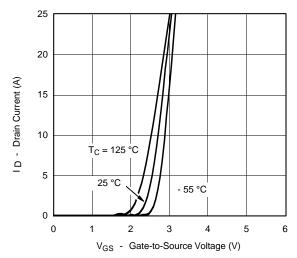
 $V_{DS}\,$  - Drain-to-Source Voltage (V)

### Output Characteristics

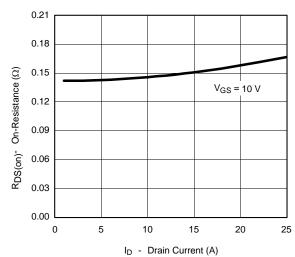


Transconductance

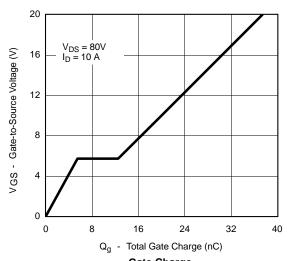




**Transfer Characteristics** 



On-Resistance vs. Drain Current

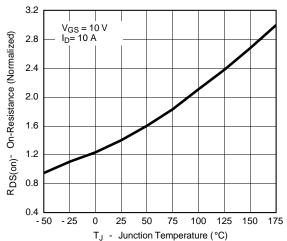


Gate Charge



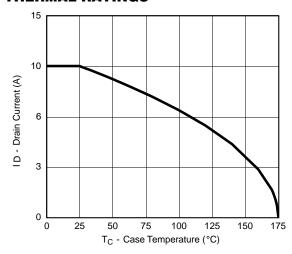
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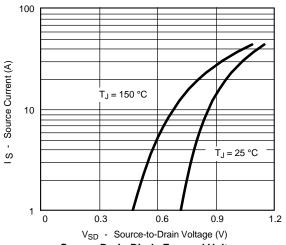


On-Resistance vs. Junction Temperature

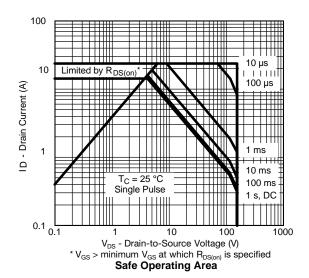
# THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage

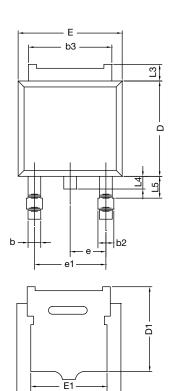


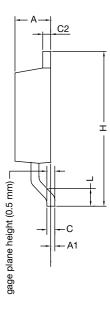
Normalized Thermal Transient Impedance, Junction-to-Case





# **TO-252AA CASE OUTLINE**





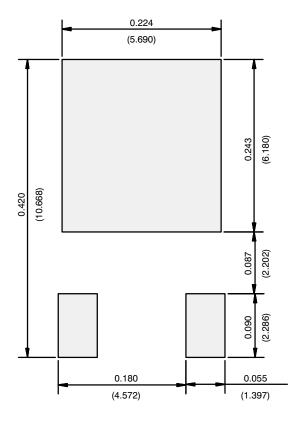
	MILLIN	METERS	INCHES				
DIM.	MIN.	MAX.	MIN.	MAX.			
Α	2.18	2.38	0.086	0.094			
A1	-	0.127	-	0.005			
b	0.64	0.88	0.025	0.035			
b2	0.76	1.14	0.030	0.045			
b3	4.95	5.46	0.195	0.215			
С	0.46	0.61	0.018	0.024			
C2	0.46	0.89	0.018	0.035			
D	5.97	6.22	0.235	0.245			
D1	5.21	-	0.205	-			
Е	6.35	6.73	0.250	0.265			
E1	4.32	-	0.170	-			
Н	9.40	10.41	0.370	0.410			
е	2.28	BSC	0.090	90 BSC			
e1	4.56	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070			
L3	0.89	1.27	0.035	0.050			
L4	-	1.02	-	0.040			
L5	1.14	1.52	0.045	0.060			
ECN: X12-0247-Rev. M, 24-Dec-12							

### DWG: 5347 Note

• Dimension L3 is for reference only.



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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